

HiPerFRED Module

V_{RRM}	=	600 V
I_{DAV}	=	86 A
t_{rr}	=	35 ns

Fast Recovery Epitaxial Diode
 Low Loss and Soft Recovery
 3~ Rectifier Bridge

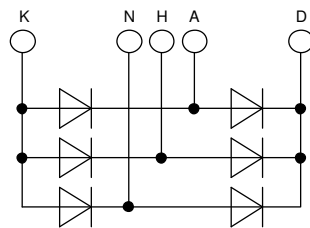
Part number

VUE75-06NO7



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Supplies for DC power equipment
- Input and output rectifiers for high frequency
- Battery DC power supplies
- Field supply for DC motors

Package: ECO-PAC1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V	
I_R	reverse current, drain current	$V_R = 600 V$	$T_{VJ} = 25^{\circ}C$		250	μA	
		$V_R = 600 V$	$T_{VJ} = 150^{\circ}C$		1	mA	
V_F	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		1.57	V	
		$I_F = 90 A$			2.20	V	
		$I_F = 30 A$	$T_{VJ} = 150^{\circ}C$		1.22	V	
		$I_F = 90 A$			1.75	V	
I_{DAV}	bridge output current	$T_C = 100^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 150^{\circ}C$		86	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.98	V	
r_F	slope resistance				8	m Ω	
R_{thJC}	thermal resistance junction to case				0.9	K/W	
R_{thCH}	thermal resistance case to heatsink			0.30		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		140	W	
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		250	A	
C_J	junction capacitance	$V_R = 400 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		26	pF	
I_{RM}	max. reverse recovery current	} $I_F = 30 A; V_R = 300 V$ $-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		6	A	
			$T_{VJ} = 100^{\circ}C$		10	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		35	ns	
			$T_{VJ} = 100^{\circ}C$		100	ns	



Package ECO-PAC1		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				19		g
M_D	mounting torque		1.4		2	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3600 3000			V V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUE75-06NO7	VUE75-06NO7	Box	25	482846

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Fast Diode

$V_{0\ max}$	threshold voltage	0.98	V
$R_{0\ max}$	slope resistance *	6	mΩ

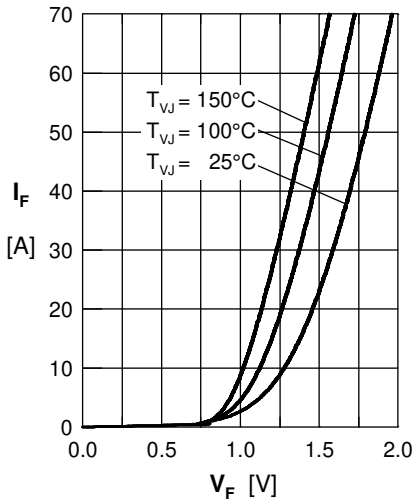
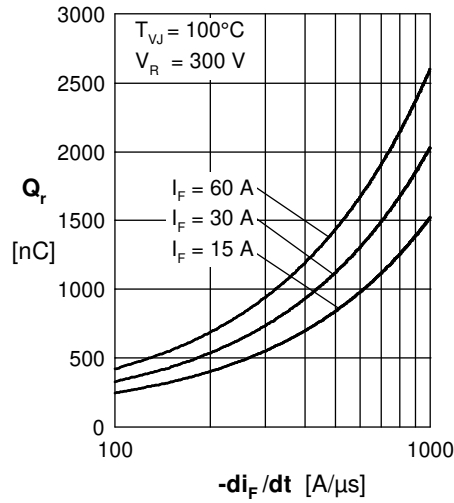
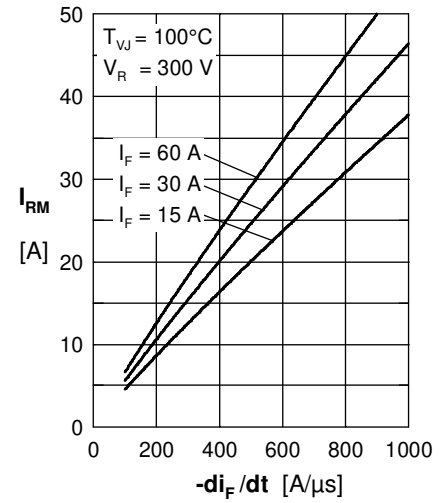
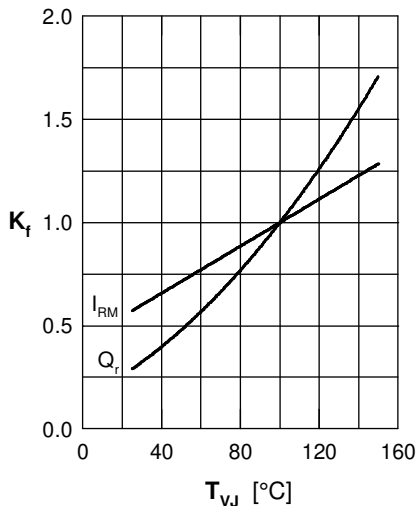
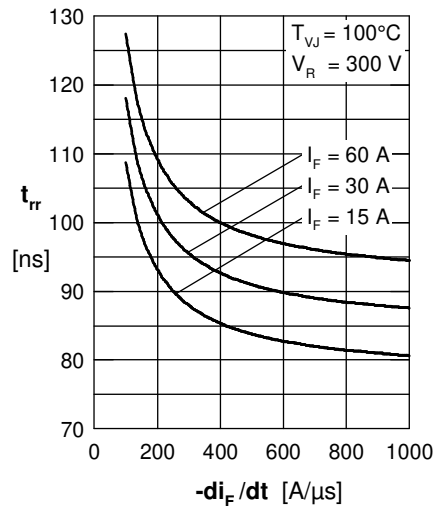
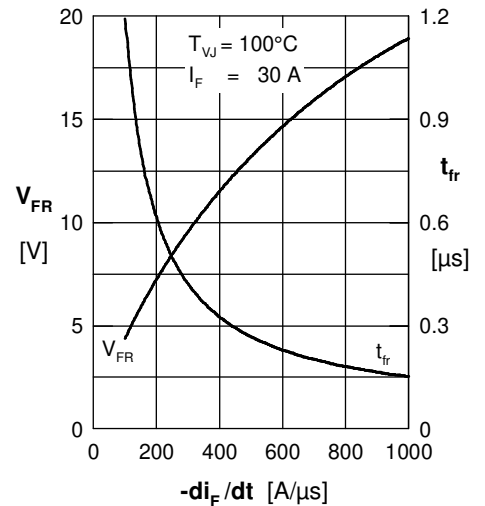
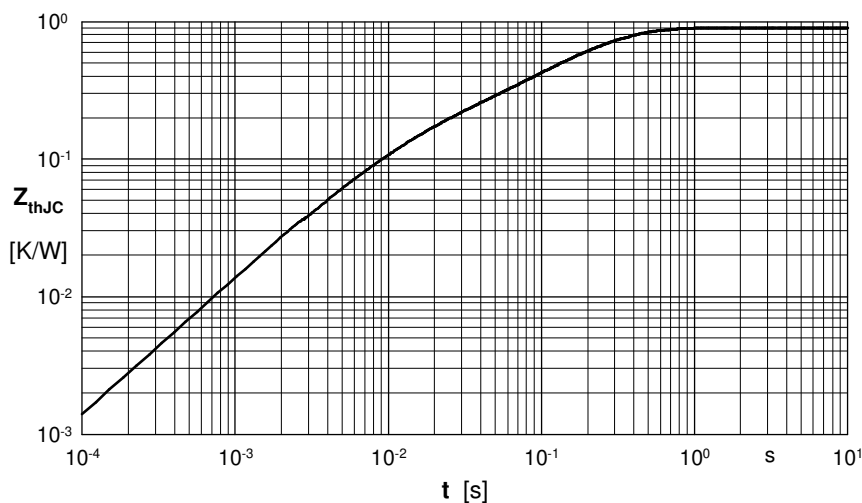
Fast Diode

 Fig. 1 Forward current I_F vs. V_F

 Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

 Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

 Fig. 6 Peak forward voltage V_{FR} and t_{fr} vs. $-di_F/dt$


Fig. 7 Transient thermal resistance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.3012	0.0052
2	0.1160	0.0003
3	0.0241	0.0004
4	0.4586	0.0092